

	No.2487A	<h1 style="margin: 0;">2SC3466</h1> <p style="margin: 0;">NPN Triple Diffused Planar Type Silicon Transistor</p> <p style="margin: 0;">Switching Regulator Applications</p>
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**Features**

- . High breakdown voltage and high reliability
- . Fast switching speed
- . Wide ASO

**Absolute Maximum Ratings at Ta=25°C**

			unit
Collector-to-Base Voltage	$V_{CB0}$	1200	V
Collector-to-Emitter Voltage	$V_{CEO}$	650	V
Emitter-to-Base Voltage	$V_{EBO}$	7	V
Collector Current	$I_C$	8	A
Peak Collector Current	$i_{cp}$	20	A
Base Current	$I_B$	3	A
Collector Dissipation	$P_C$	120	W
Junction Temperature	$T_J$	150	°C
Storage Temperature	$T_{stg}$	-55 to +150	°C

$PW \leq 300\mu s, \text{duty cycle} \leq 10\%$

$T_c = 25^\circ C$

**Electrical Characteristics at Ta=25°C**

			min	typ	max	unit
Collector Cutoff Current	$I_{CBO}$	$V_{CB}=650V, I_E=0$			100	μA
Emitter Cutoff Current	$I_{EBO}$	$V_{EB}=5V, I_C=0$			100	μA
DC Current Gain	$h_{FE1}$	$V_{CE}=5V, I_C=1A$	10*		40*	
	$h_{FE2}$	$V_{CE}=5V, I_C=4A$	6			
Gain-Bandwidth Product	$f_T$	$V_{CE}=10V, I_C=1A$		5		MHz
Output Capacitance	$c_{ob}$	$V_{CB}=10V, f=1MHz$		120		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=4A, I_B=0.8A$			3.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=4A, I_B=0.8A$			1.5	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=1mA, I_E=0$	1200			V

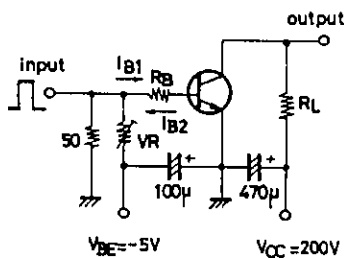
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\*: The 2SC3466 is classified by 1A  $h_{FE}$  as follows:

10 K 20	15 L 30	20 M 40
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**Switching Time Test Circuit**

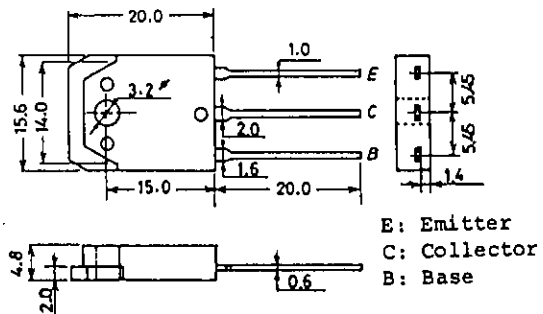
$PW=20\mu s, \text{duty factor} \leq 1\%$



Unit (Resistance : Ω, Capacitance : F)

**Package Dimensions 2022**

(unit:mm)

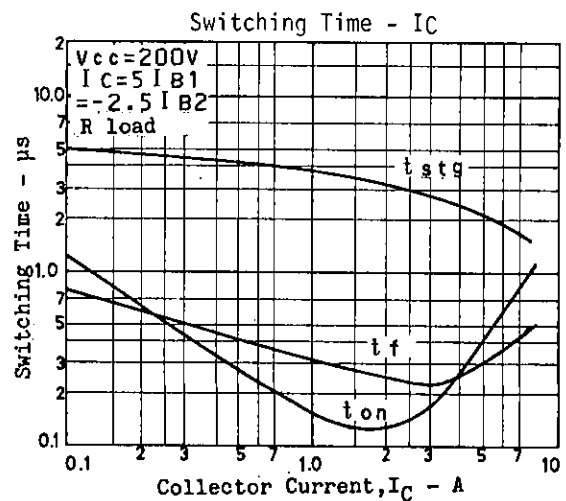
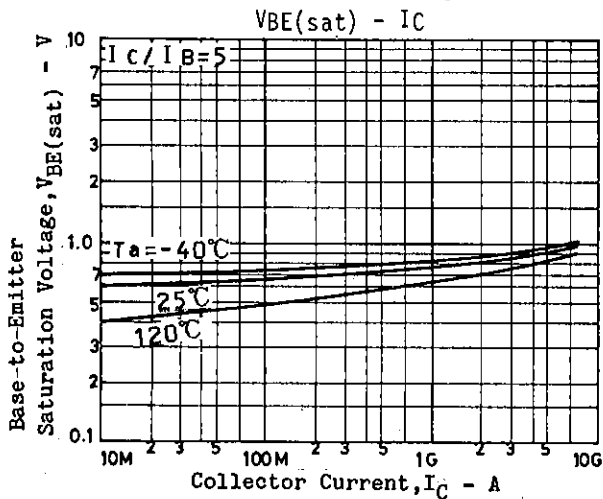
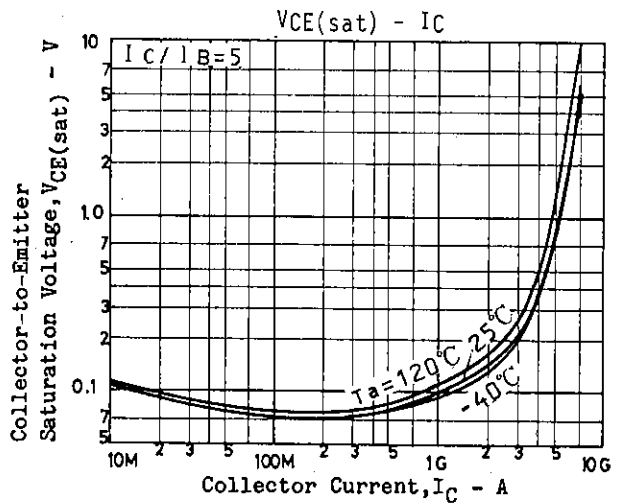
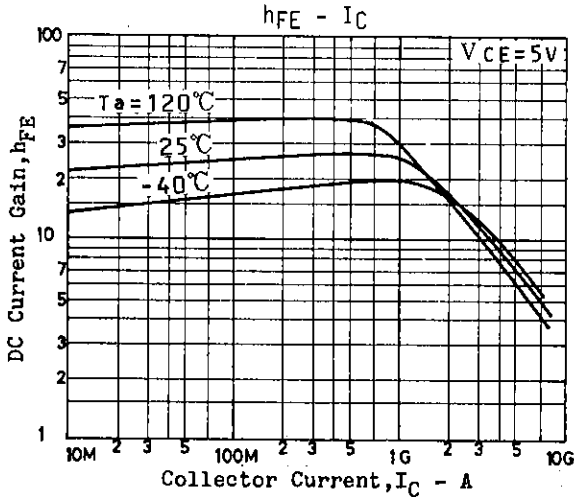
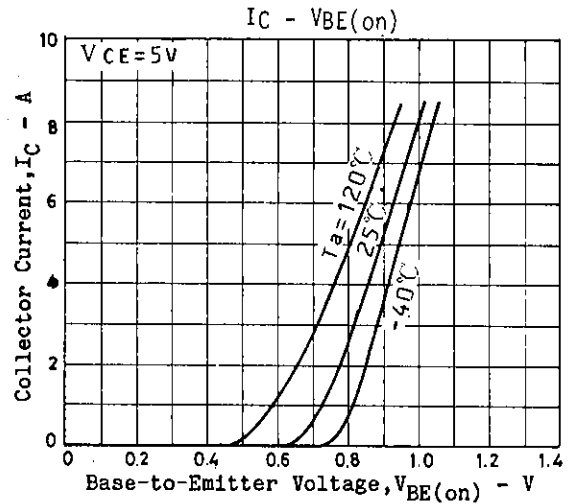
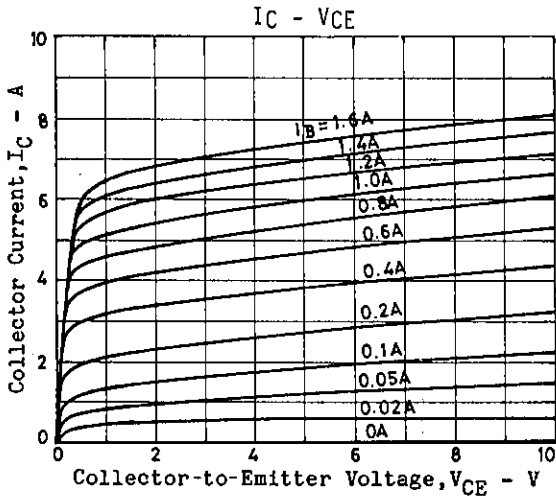


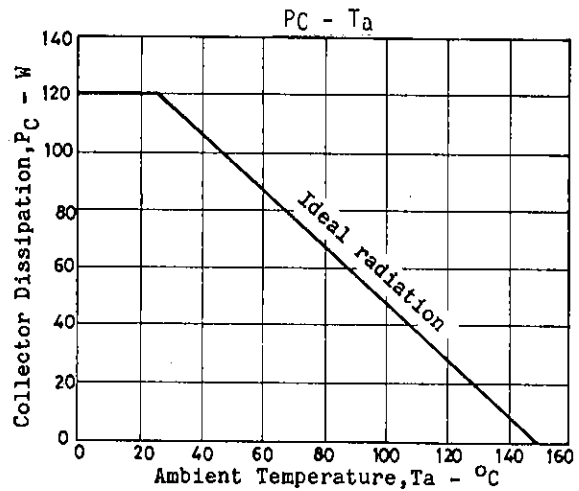
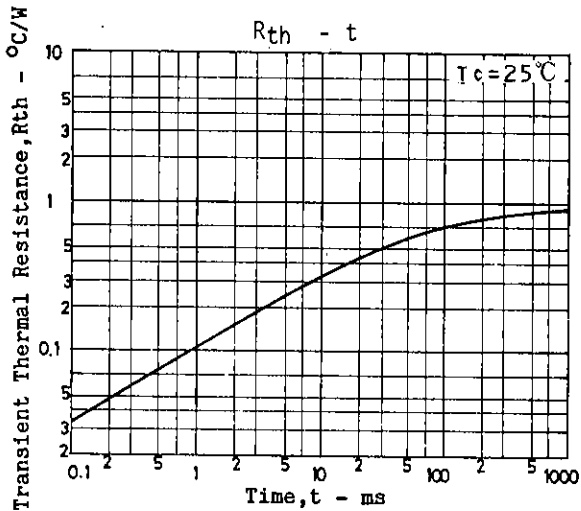
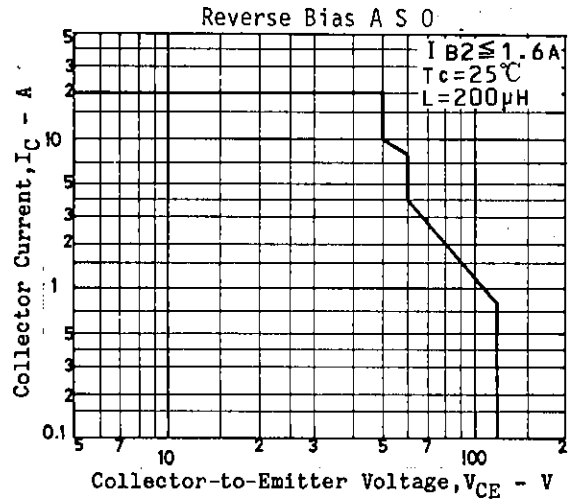
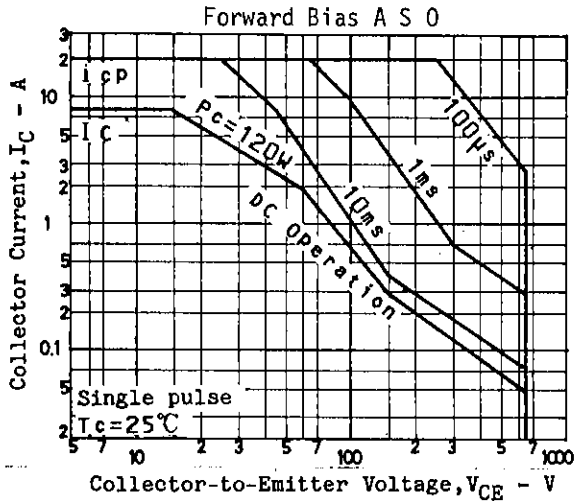
E: Emitter  
C: Collector  
B: Base

SANYO: TO3PB

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			min	typ	max	unit
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=5mA, R_{BE}=\infty$	650			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=1mA, I_C=0$	7			V
Turn-on Time	$t_{on}$	$V_{CC}=200V, 5I_{B1}=-2.5I_{B2}$ $=I_C=4A, R_L=50ohms$			1.0	$\mu s$
Storage Time	$t_{stg}$				4.0	$\mu s$
Fall Time	$t_f$				0.7	$\mu s$





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